

SiC Schottky Barrier Rectifier

Reverse Voltage - 650V

Forward Current - 10A

Features

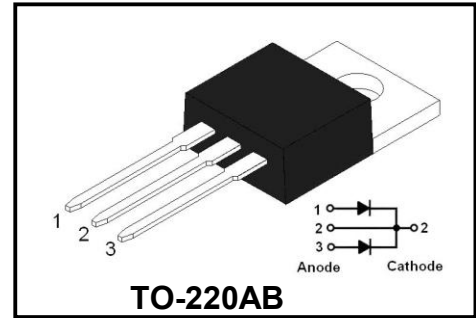
- ◆ Reverse withstand voltage 650V
- ◆ Zero reverse recovery current
- ◆ High working frequency
- ◆ Switch characteristics are not affected by temperature
- ◆ Fast switching speed
- ◆ Positive temperature coefficient of positive pressure drop

Advantages

- ◆ Very low switching loss
- ◆ Higher efficiency
- ◆ Low dependence of the system on the heat sink
- ◆ No thermal collapse in parallel devices

Application

- ◆ Switching mode power supply, AC/DC converter
- ◆ Power factor correction
- ◆ Motor drive
- ◆ PV inverter and wind turbine



Product Specification Classification

Part Number	Package	Marking	Pack
YFWD310065CT	TO-220AB	YFW D310065CT XXXXX	1000PCS/box

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Test conditions	Value	Unit
Peak repetitive reverse voltage	V_{RRM}		650	V
Working Peak Reverse voltage	V_{RWM}		650	V
DC Blocking Voltage	V_{DC}		650	V
Average rectified output current	$I_{F(AV)}$	Ta=25°C	33	A
		Ta=125°C	15	
		Ta=150°C	10	
Forward repetitive peak current	I_{FRM}	T _C =25°C, tp=10ms, Half Sine Wave	50	A
		T _C =110°C, tp=10ms, Half Sine Wave	28	
Forward surge current	I_{FSM}	T _C =25°C, tp=10ms, Half Sine Wave	90	A
		T _C =110°C, tp=10ms, Half Sine Wave	65	
Power dissipation	P_{tot}	Ta=25°C	98	W
		Ta=110°C	45	
Junction temperature	T _j		-55 ~ +175	°C
Storage temperature	T _{stg}		-55 ~ +175	°C

Thermal characteristics

Parameter	Symbol	Vaule	Unit
Thermal Resistance - Junction to Case	$R_{\theta JC}$	2.03	$^{\circ}C/W$

Electrical Characteristics (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Forward voltage	V_F	$I_F = 10 A, T_j = 25^{\circ}C$ $I_F = 10 A, T_j = 175^{\circ}C$		1.45 1.61	1.6 1.8	V
Reverse current	I_R	$V_R = 650V, T_j = 25^{\circ}C$ $V_R = 650V, T_j = 175^{\circ}C$		1 12	60 220	μA
Total capacitive charge	Q_C	$V_R = 400V, I_F = 10A$ $di/dt = 500A/\mu s, T_j = 25^{\circ}C$		39		nC
Total capacitance	C	$V_R = 0V, T_j = 25^{\circ}C, f = 1MHz$ $V_R = 200V, T_j = 25^{\circ}C, f = 1MHz$ $V_R = 400V, T_j = 25^{\circ}C, f = 1MHz$		762 75 54		pF

Typical Characteristics

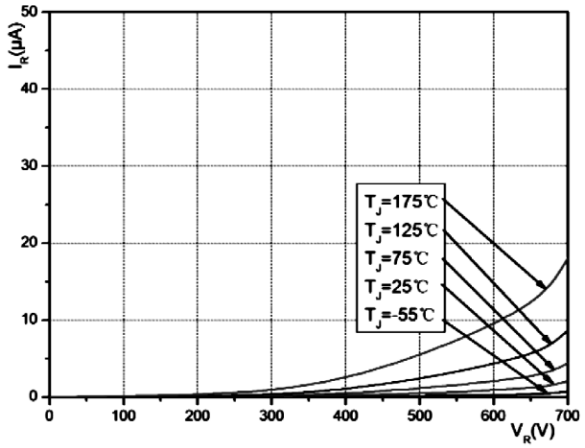


Figure 1. Forward Characteristics

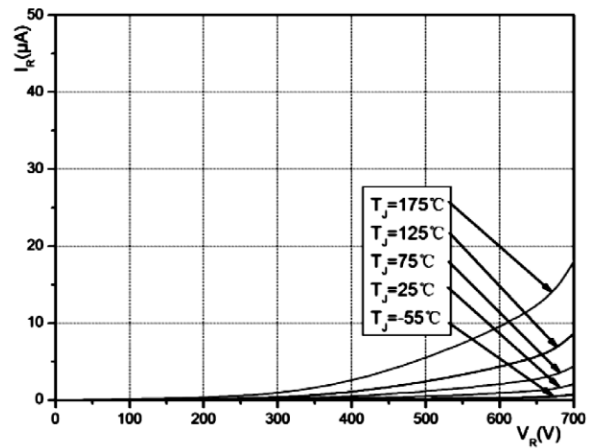


Figure 2. Reverse Characteristics

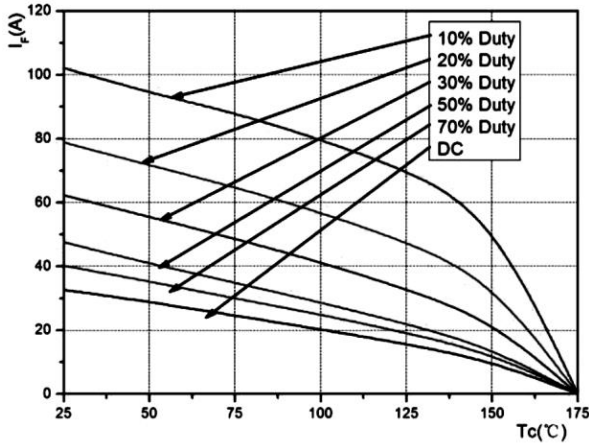


Figure 3. Load current

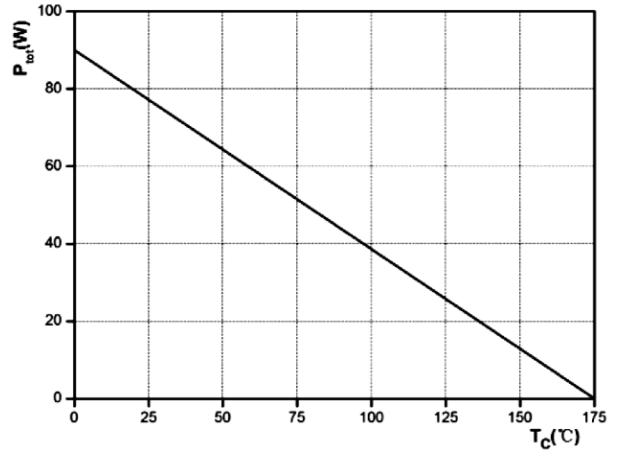


Figure 4. Dissipated power curve

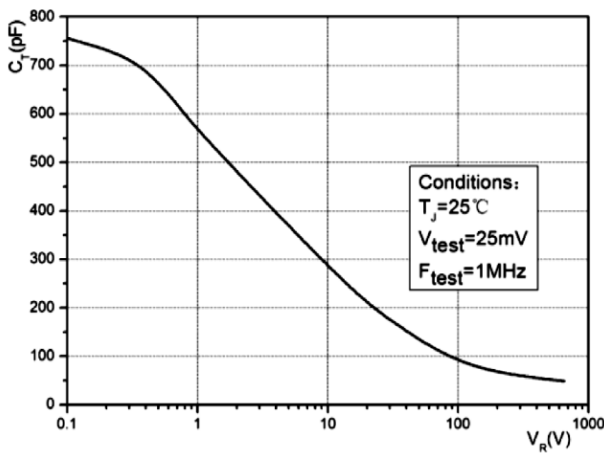


Figure 5. Capacitance vs reverse voltage

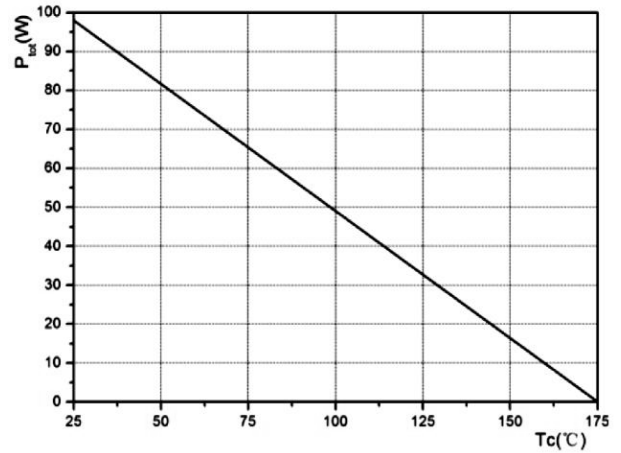


Figure 6. Thermal Impedance Junction-to-Case

Package Dimensions

TO-220AB

Dim	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.34	4.67	0.171	0.184
A1	2.52	2.82	0.099	0.111
b	0.71	0.91	0.028	0.036
b1	1.17	1.37	0.046	0.054
c	0.30	0.50	0.012	0.020
c1	1.17	1.37	0.046	0.054
D	9.90	10.20	0.390	0.402
E	8.50	8.90	0.335	0.350
E1	12.00	12.50	0.472	0.492
e	2.44	2.64	0.096	0.104
e1	4.88	5.28	0.192	0.208
F	2.60	2.80	0.102	0.110
L	13.20	13.80	0.520	0.543
L1	3.80	4.20	0.150	0.165
Φ	3.60	3.96	0.142	0.156